

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device includes  
a semiconductor region of a first conductivity type.  
A first insulated-gate field effect transistor having  
5 a source/drain region of a second conductivity type  
connected to an output terminal is formed on the  
semiconductor region. Further, a semiconductor region  
of a second conductivity type connected to the gate of  
the transistor is formed adjacent to the source/drain  
10 region of the transistor on the semiconductor region.